

## 清华大学高等研究院

Institute for Advanced Study, Tsinghua University

## 学术报告

Title:	Energy Level Alignment and Atomic-Scale Interactions at Interfaces from First Principles	
Speaker:	Su Ying Quek	(National University of Singapore)
Time:	10:00am, Monday, July 22, 2019	
Venue:	Conference Hall 213, Science Building, Tsinghua University	

## Abstract

Interfaces are everywhere around us. The alignment of energy levels at interfaces in devices determines the device contact resistance, while the atomic-scale interactions at interfaces influence macroscopic experimental observables. In this talk, I will describe how my group has used first principles calculations to study a variety of interfacial phenomena in organic-inorganic heterostructures as well as 2D material systems. Energy level alignment (ELA) is an important but challenging problem from both theoretical and experimental points of view. Theoretically, it is widely known that quantitative predictions of ELA require methods beyond standard density functional theory, the work-horse of first principles calculations. ELA can be predicted quantiatively using manybody perturbation theory in the GW approximation, but GW calculations are computationally very expensive for large interface systems. In this work, we develop approaches to predict ELA at the GW level using computationally tractable methods. Using a simple but powerful approach, called XAF-GW [1], we can perform GW calculations of large interface systems without strong covalent bonds. We show analytically that the approach works for hybridized systems up to first order in the overlap matrices, and validate our approach using bilayer black phorphorus, where interface hybridization takes place. XAF-GW allows us to perform GW calculations of PTCDA layers on Au and Ag substrates, as well as on graphite-supported WSe2 substrates. We further propose simple back-of-the-envelope estimates of the ELA for small physisorbed molecules on any substrate, and study the non-local screening effects of 2D materials [2]. The physics of screening at hybridized organic-metal interfaces is also investigated [3]. Besides ELA, atomic-scale interactions at interfaces can also lead to interesting experimentally observable properties, even in 2D layered materials where interfacial interactions are thought to be weak. We predict an electric-field induced Dirac cone in black phosphorus thin films which we show arises from quantum confinement and anisotropic interlayer interactions [4], that are unusually large in this material. The unusually large interlayer interactions were deduced from the computed frequencies of interlayer breathing modes [5], that were confirmed in experiment. Such interlayer interactions also result in experimentally observable stacking sequence dependent frequency trends in the interlayer shear modes for 2D materials in general [6]. Surface effects resulting from the removal of interlayer interactions are also responsible for anomalous frequency trends in transition metal dichalcogenide systems [7].

[1] Journal of Chemical Theory and Computation, 15, 3824 (2019)

[2] 2D Materials, 6, 035036 (2019)[4] Scientific Reports 5, 11699 (2015)

[3] J Phys Chem C, 121, 13125 (2017)

[5] Nano Letters, 15, 3931 (2015)

[7] Physical Review B, 88, 075320 (2013)

[6] Scientific Reports 5, 14565 (2015), Advanced Materials, 27, 4502 (2015)

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